NSN 5961-01-343-8875

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-343-8875 **Inclosure Material:** Glass **Overall Length:** Between 0.293 inches and 0.357 inches **Terminal Length:** Between 1.000 inches and 1.625 inches **Overall Diameter:** Between 0.215 inches and 0.235 inches **Function For Which Designed:** Transient suppressor Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-13 **Mounting Method: Terminal Features Provided:** Hermetically sealed case and quality assurance level txv **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 49.4 breakdown voltage, dc **Voltage Tolerance In Percent:** -5.0/+5.0 **Current Rating Per Characteristic:** 5.00 microamperes forward current, average peak **Power Rating Per Characteristic:** 1.0 watts small-signal input power, common-collector major **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/507 government specification Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: